



## **IRFB3306PBF Information**

Part Number IRFB3306PBF

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 60V 120A TO-220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

For Reference Only

Website: https://www.heisener.com

E-mail: salesdept@heisener.com



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# **IRFB3306PBF Specifications**

Manufacturer Part NumberIRFB3306PBFManufacturerInfineon TechnologiesCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-220-3SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C120A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 150µAGate Charge (Qg) (Max) @ Vgs120nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4520pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)230W (Tc)Rds On (Max) @ Id, Vgs4.2 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220ABReport errors?		
Category         Discrete Semiconductor Products           Package         TO-220-3           Series         HEXFET?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         120A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 150µA           Gate Charge (Qg) (Max) @ Vgs         120nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         4520pF @ 50V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         230W (Tc)           Rds On (Max) @ Id, Vgs         4.2 mOhm @ 75A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220AB           Package / Case         TO-220-3	Manufacturer Part Number	IRFB3306PBF
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Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

#### **IRFB3306PBF** Guarantees



### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## **IRFB3306PBF Payment Methods**





















## **IRFB3306PBF Shipping Methods**













If you have any question about IRFB3306PBF, please do not hesitate to contact us!

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